

ABSTRACT

A semiconductor device 1 obtained by depositing, on a substrate 2, a gate electrode 4 formed by a conductive thin film containing Mo atoms and Ag atoms, a gate insulating film 6, an α -Si:H(i) film 8, a channel protection layer 10, an α -Si:H(n) film 12, a source/drain electrode 14 formed by a conductive thin film containing Mo atoms and Ag atoms, a source/drain insulating film 16, and a drive electrode 18. By using a conductive thin film containing Mo atoms and Ag atoms, the gate electrode 4 and the source/drain electrode 14 are formed to manufacture the semiconductor device 1. Thus, the conductive thin film for a semiconductor device, having high adhesion strength to a substrate, an insulating layer, and the like, a semiconductor device which operates stably without deteriorating the performance, and a method of efficiently manufacturing the conductive thin film and the semiconductor device can be provided.

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